

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The **ASI BLV11** is Designed for Class C, 12.5 Volt operation in FM Amplifier Applications up to 250 MHz.

**FEATURES INCLUDE:**

- $P_G = 9.0$  dB Typical at 175 MHz
- Emitter Ballasting
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	3.0 A
$V_{CE}$	18 V
$V_{CB}$	36 V
$P_{DISS}$	37 W @ $T_C = 25^\circ\text{C}$
$T_J$	$-65^\circ\text{C}$ to $+200^\circ\text{C}$
$T_{STG}$	$-65^\circ\text{C}$ to $+150^\circ\text{C}$
$\theta_{JC}$	4.6 $^\circ\text{C/W}$

**PACKAGE STYLE .375 4L FLG**

	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.220/5.59	.230/5.84
B	.785/19.94	
C	.720/18.29	.730/18.54
D	.970/24.64	.980/24.89
E		.385/9.78
F	.004/0.10	.006/0.15
G	.085/2.16	.105/2.67
H	.160/4.06	.180/4.57
I		.280/7.11
J	.240/6.10	.255/6.48

1 = Collector 2 = Base  
3 & 4 = Emitter

**ORDER CODE: ASI10492**

**CHARACTERISTICS**  $T_C = 25^\circ\text{C}$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 20$ mA	36			V
$BV_{CES}$	$I_C = 50$ mA	36			V
$BV_{CEO}$	$I_C = 50$ mA	18			V
$BV_{EBO}$	$I_E = 5.0$ mA	4.0			V
$I_{CBO}$	$V_{CB} = 15$ V			2.0	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 250$ mA	5.0	50		---
$C_{ob}$	$V_{CB} = 12.5$ V $f = 1.0$ MHz		45		pF
$P_G$	$V_{CE} = 13.5$ V $P_{OUT} = 15$ W $f = 175$ MHz	8.0	9.0		dB
$\eta_C$		60	65		%